

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max       | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|--|
| 60V               | 50mΩ @ V <sub>GS</sub> = 10V  | 18A  |
|                   | 63mΩ @ V <sub>GS</sub> = 4.5V | 16A  |

## Description and Applications


This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

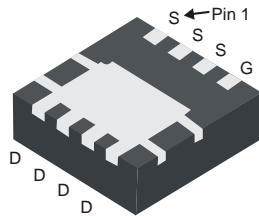
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

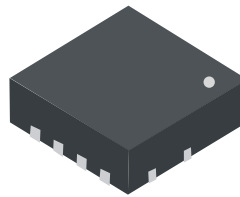
## Mechanical Data

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.03 grams (Approximate)

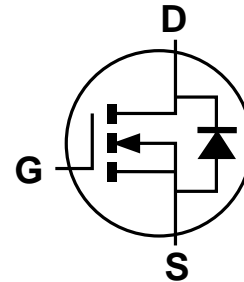


Bottom View

PowerDI3333-8



Top View



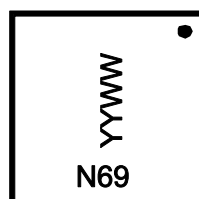
Equivalent Circuit

## Ordering Information (Note 5)

| Part Number    | Case          | Packaging         |
|----------------|---------------|-------------------|
| DMN6069SFGQ-7  | PowerDI3333-8 | 2,000/Tape & Reel |
| DMN6069SFGQ-13 | PowerDI3333-8 | 3,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



N69 = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 16 = 2016)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |              |  | Symbol           | Value      | Unit |
|---|--------------|--|------------------|------------|------|
| Drain-Source Voltage                                    |              |  | V <sub>DSS</sub> | 60         | V    |
| Gate-Source Voltage                                     |              |  | V <sub>GSS</sub> | ±20        | V    |
| Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 5.6<br>4.5 | A    |
|   | Steady State | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +70°C | I <sub>D</sub>   | 18<br>14.5 | A    |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)     |              |  | I <sub>DM</sub>  | 25         | A    |
| Maximum Continuous Body Diode Forward Current (Note 7)  |              |  | I <sub>S</sub>   | 2.5        | A    |
| Avalanche Current (Note 8) L = 0.1mH                    |              |  | I <sub>AS</sub>  | 12         | A    |
| Repetitive Avalanche Energy (Note 8) L = 0.1mH          |              |  | E <sub>AS</sub>  | 7.2        | mJ   |

**Thermal Characteristics**

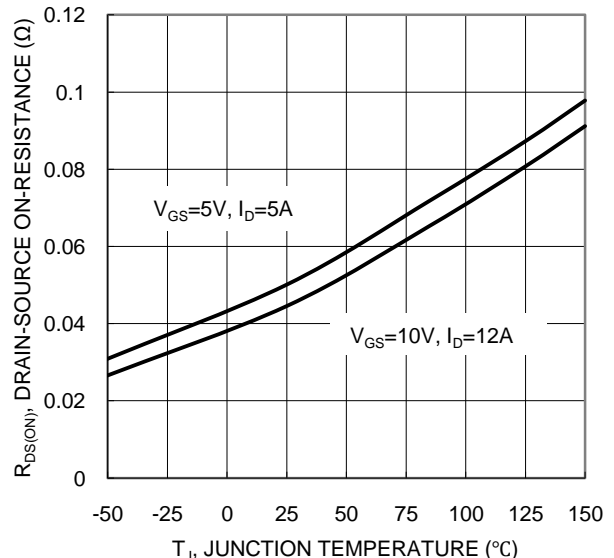
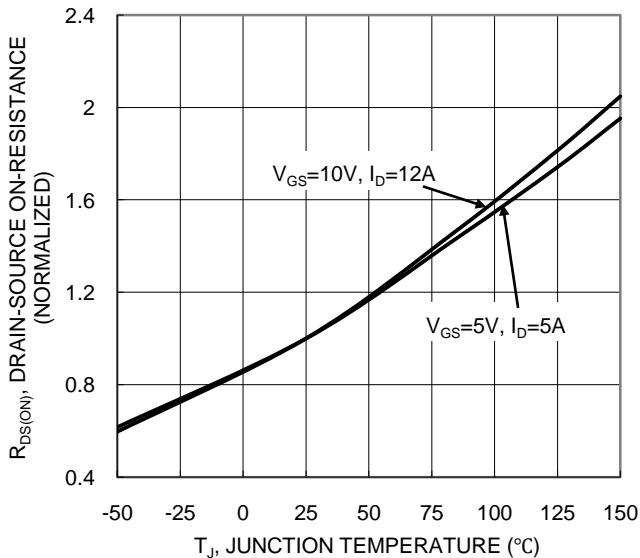
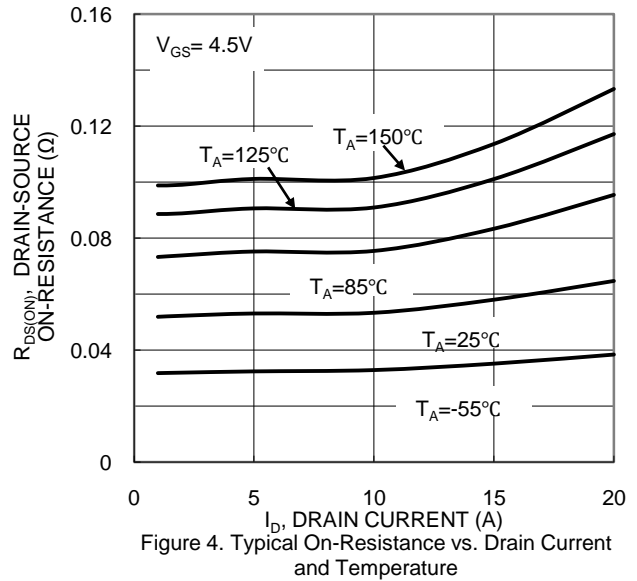
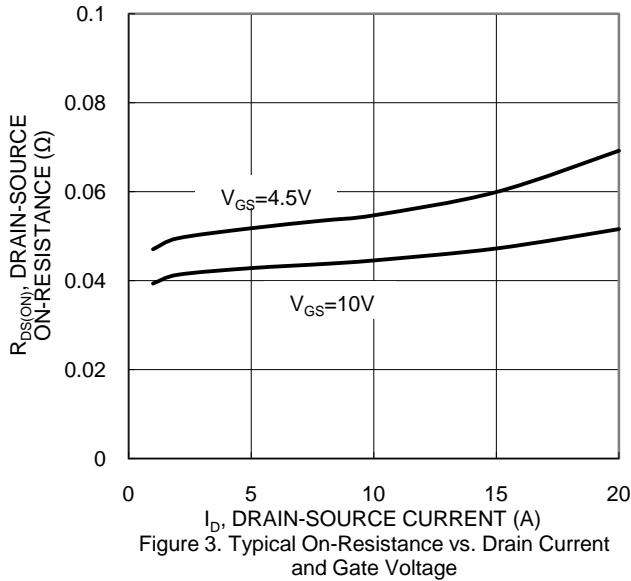
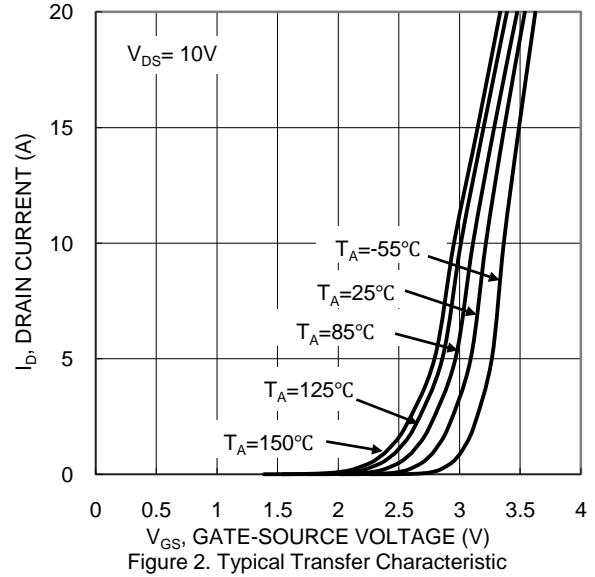
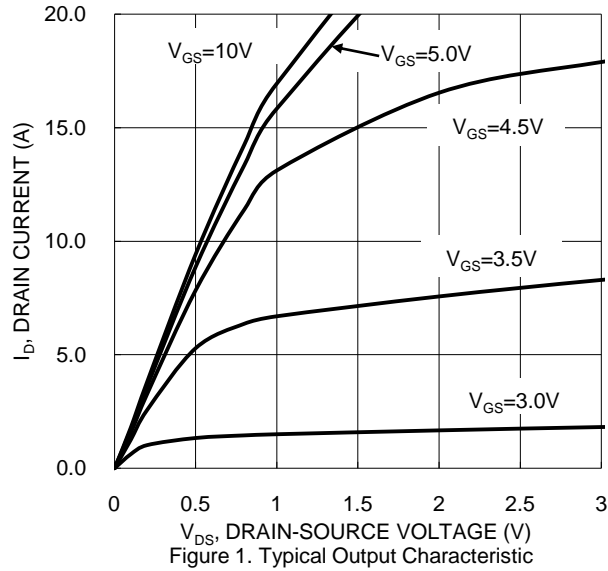
| Characteristic                                   |              | Symbol                            | Value       | Unit |
|--|--------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 6)                 |              | P <sub>D</sub>                    | 0.93        | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R <sub>θJA</sub>                  | 134         | °C/W |
|  | t<10s        |                                   | 82          |      |
| Total Power Dissipation (Note 7)                 |              | P <sub>D</sub>                    | 2.4         | W    |
| Thermal Resistance, Junction to Ambient (Note 7) | Steady State | R <sub>θJA</sub>                  | 53          | °C/W |
|  | t<10s        |                                   | 33          |      |
| Thermal Resistance, Junction to Case             |              | R <sub>θJC</sub>                  | 5           |      |
| Operating and Storage Temperature Range          |              | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

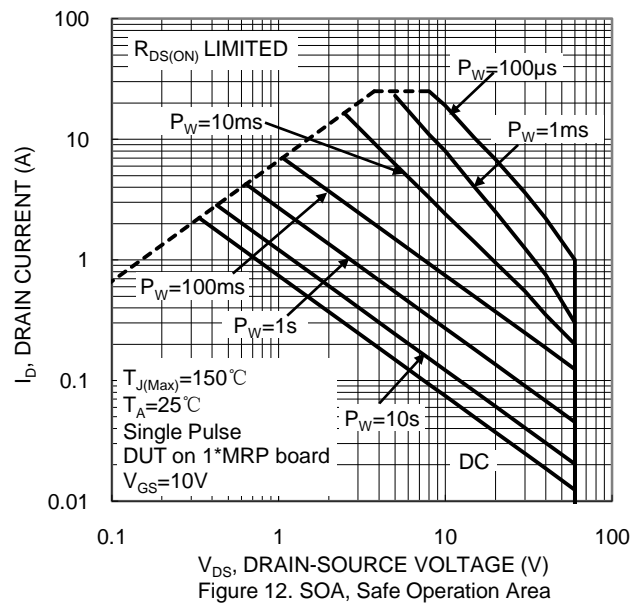
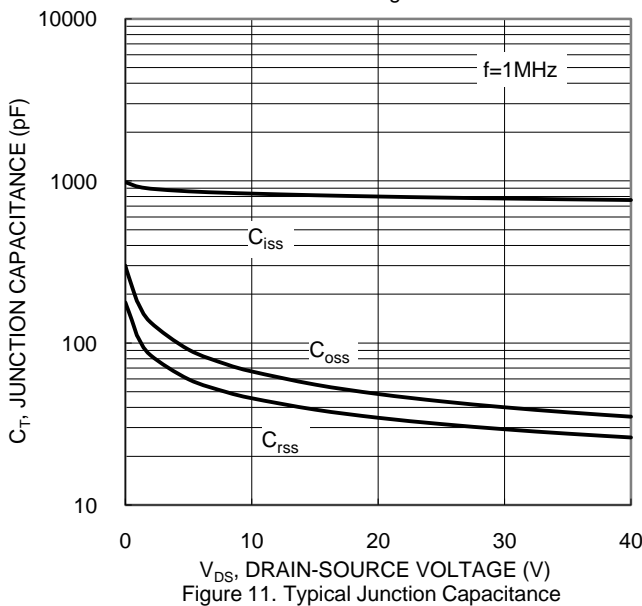
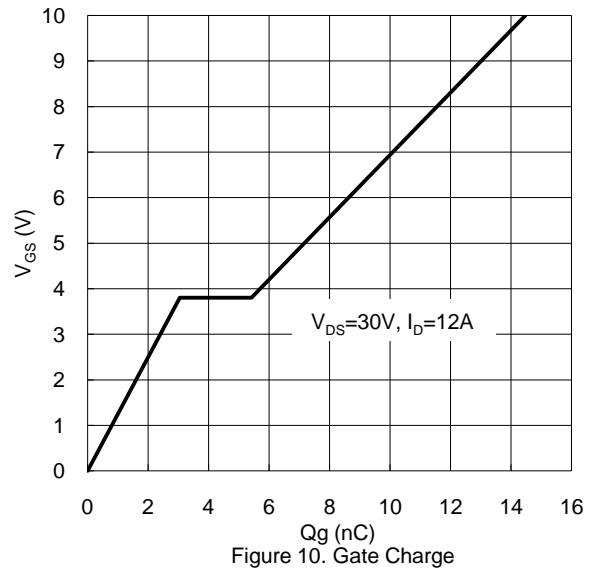
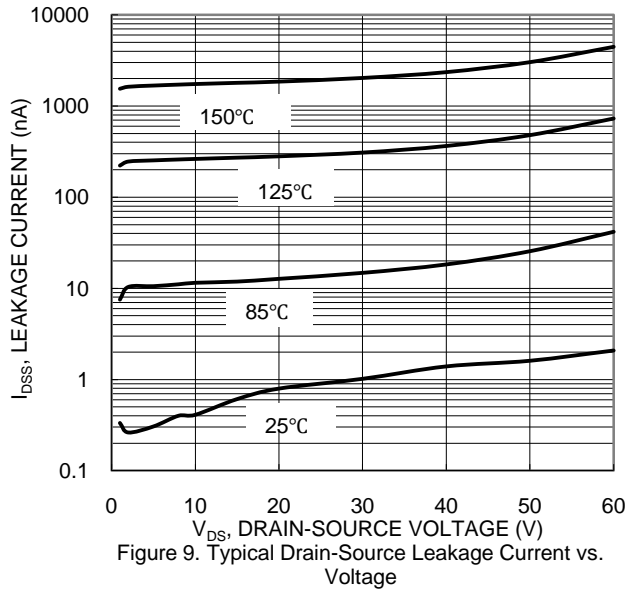
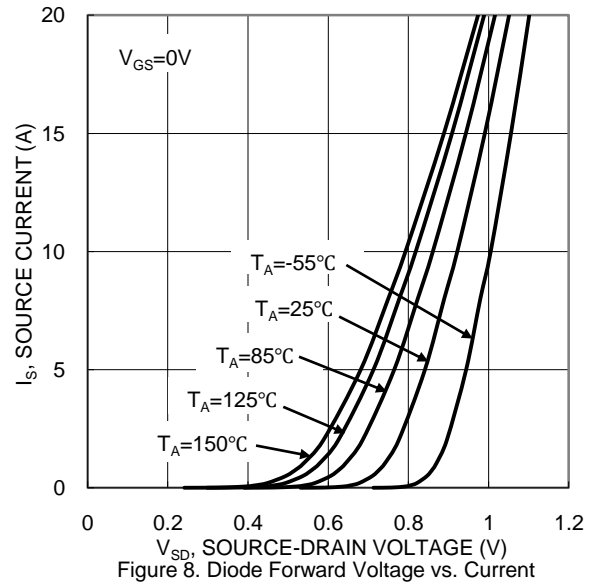
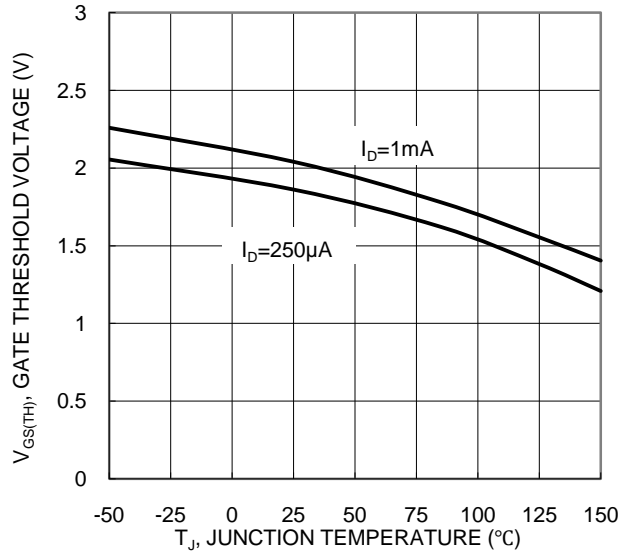
- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

**Electrical Characteristics** ( $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic   | Symbol       | Min | Typ | Max       | Unit       | Test Condition   |
|--|--------------|-----|-----|-----------|------------|--|
| <b>OFF CHARACTERISTICS</b> (Note 9)                        |              |     |     |           |            |  |
| Drain-Source Breakdown Voltage                             | $BV_{DSS}$   | 60  | —   | —         | V          | $V_{GS} = 0V, I_D = 250\mu A$                            |
| Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$  | $I_{DSS}$    | —   | —   | 1         | $\mu A$    | $V_{DS} = 60V, V_{GS} = 0V$                              |
| Zero Gate Voltage Drain Current $T_J = +150^\circ\text{C}$ | $I_{DSS}$    | —   | —   | 100       | $\mu A$    | $V_{DS} = 60V, V_{GS} = 0V$                              |
| Gate-Source Leakage  | $I_{GSS}$    | —   | —   | $\pm 100$ | nA         | $V_{GS} = \pm 20V, V_{DS} = 0V$                          |
| <b>ON CHARACTERISTICS</b> (Note 9)                         |              |     |     |           |            |  |
| Gate Threshold Voltage                                     | $V_{GS(TH)}$ | 1   | —   | 3         | V          | $V_{DS} = V_{GS}, I_D = 250\mu A$                        |
| Static Drain-Source On-Resistance                          | $R_{DS(ON)}$ | —   | 39  | 50        | m $\Omega$ | $V_{GS} = 10V, I_D = 4.5A$                               |
|  |              | —   | 47  | 63        |            | $V_{GS} = 4.5V, I_D = 3A$                                |
| Diode Forward Voltage                                      | $V_{SD}$     | —   | —   | 1.1       | V          | $V_{GS} = 0V, I_S = 2.5A$                                |
| On State Drain Current (Note 10)                           | $I_{D(ON)}$  | 20  | —   | —         | A          | $V_{DS} \geq 5V, V_{GS} = 10V$                           |
| <b>DYNAMIC CHARACTERISTICS</b> (Note 10)                   |              |     |     |           |            |  |
| Input Capacitance  | $C_{iss}$    | —   | 740 | 1,480     | pF         | $V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz$                  |
| Output Capacitance   | $C_{oss}$    | —   | 40  | 80        | pF         |  |
| Reverse Transfer Capacitance                               | $C_{rss}$    | —   | 28  | 55        | pF         |  |
| Gate Resistance  | $R_g$        | —   | 2.2 | 4         | $\Omega$   | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$                     |
| Total Gate Charge ( $V_{GS} = 4.5V$ )                      | $Q_g$        | —   | 6.4 | 12        | nC         | $V_{DS} = 30V, I_D = 12A$                                |
| Total Gate Charge ( $V_{GS} = 10V$ )                       | $Q_g$        | —   | 14  | 25        | nC         |  |
| Gate-Source Charge   | $Q_{gs}$     | —   | 2.8 | 5.5       | nC         |  |
| Gate-Drain Charge  | $Q_{gd}$     | —   | 2.3 | 5         | nC         |  |
| Turn-On Delay Time   | $t_{D(ON)}$  | —   | 3.6 | 10        | ns         | $V_{DS} = 30V, I_D = 12A, V_{GS} = 10V, R_G = 6.0\Omega$ |
| Turn-On Rise Time  | $t_R$        | —   | 5.0 | 10        | ns         |  |
| Turn-Off Delay Time  | $t_{D(OFF)}$ | —   | 12  | 24        | ns         |  |
| Turn-Off Fall Time   | $t_F$        | —   | 3.3 | 10        | ns         |  |
| Body Diode Reverse Recovery Time                           | $t_{RR}$     | —   | 11  | 22        | ns         | $I_F = 4.5A, di/dt = 100A/\mu s$                         |
| Body Diode Reverse Recovery Charge                         | $Q_{RR}$     | —   | 5.1 | 10        | nC         |  |

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to product testing.





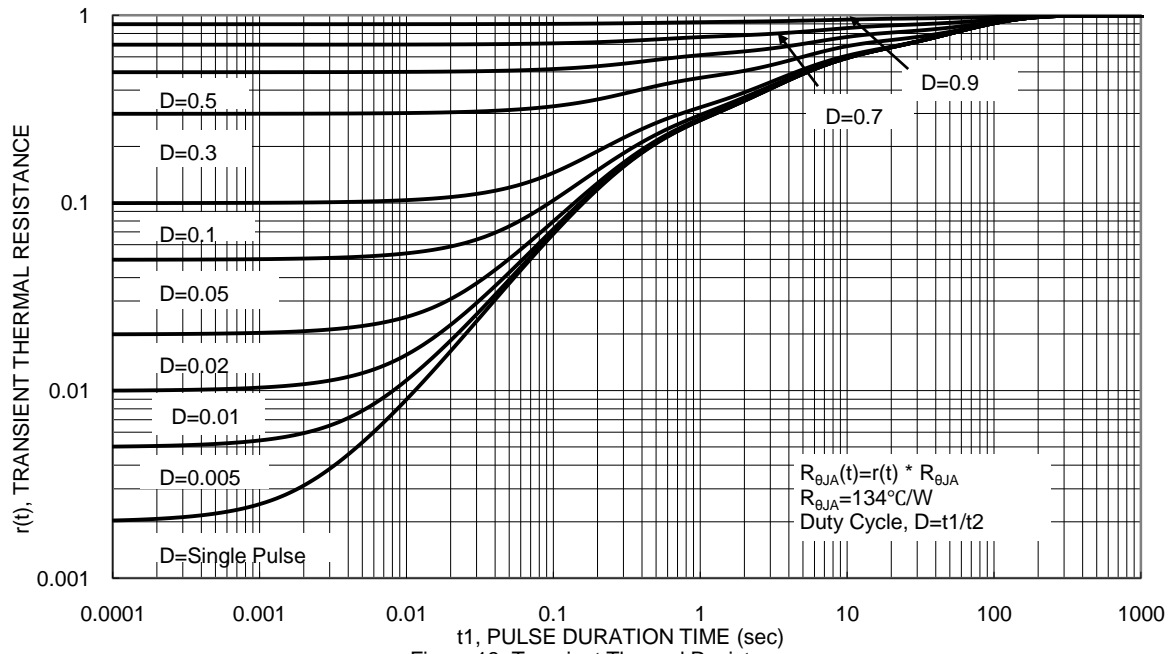
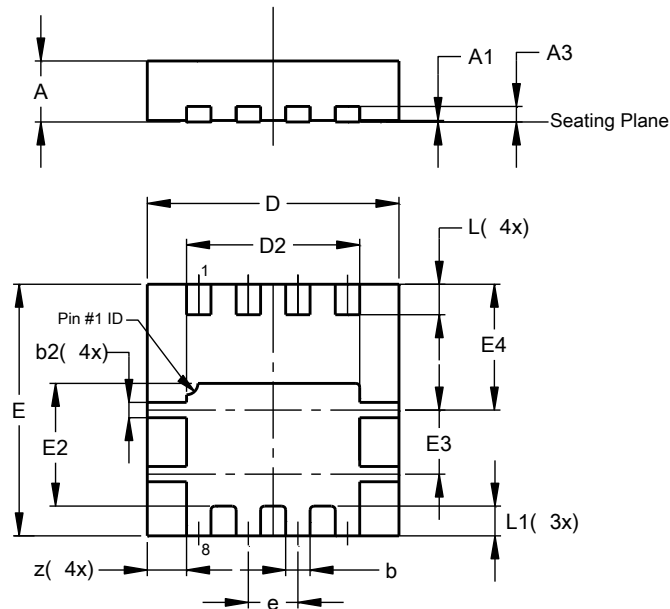


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

## PowerDI3333-8

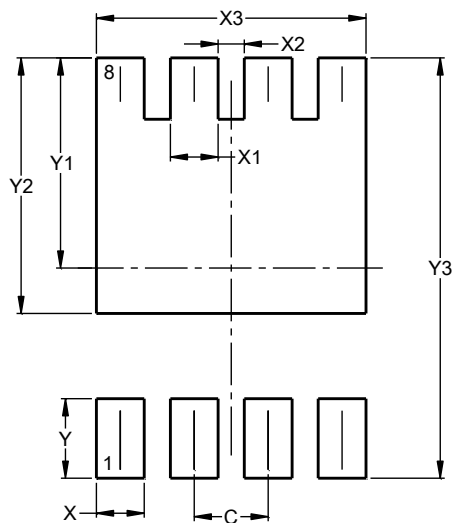


| PowerDI3333-8        |      |      |       |
|----------------------|------|------|-------|
| Dim                  | Min  | Max  | Typ   |
| A                    | 0.75 | 0.85 | 0.80  |
| A1                   | 0.00 | 0.05 | 0.02  |
| A3                   | —    | —    | 0.203 |
| b                    | 0.27 | 0.37 | 0.32  |
| b2                   | 0.15 | 0.25 | 0.20  |
| D                    | 3.25 | 3.35 | 3.30  |
| D2                   | 2.22 | 2.32 | 2.27  |
| E                    | 3.25 | 3.35 | 3.30  |
| E2                   | 1.56 | 1.66 | 1.61  |
| E3                   | 0.79 | 0.89 | 0.84  |
| E4                   | 1.60 | 1.70 | 1.65  |
| e                    | —    | —    | 0.65  |
| L                    | 0.35 | 0.45 | 0.40  |
| L1                   | —    | —    | 0.39  |
| z                    | —    | —    | 0.515 |
| All Dimensions in mm |      |      |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

## PowerDI3333-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.650         |
| X          | 0.420         |
| X1         | 0.420         |
| X2         | 0.230         |
| X3         | 2.370         |
| Y          | 0.700         |
| Y1         | 1.850         |
| Y2         | 2.250         |
| Y3         | 3.700         |

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